-100mA / -50V Digital transistors (with built-in resistors)

DTA114TM / DTA114TE / DTA114TUA DTA114TKA / DTA114TSA

●Applications

Inverter, Interface, Driver

●Features

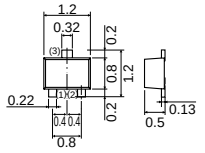
1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
3) Only the on/off conditions need to be set for operation, making the device design easy.

●Structure

PNP epitaxial planar silicon transistor (Resistor built-in type)

●External dimensions (Unit : mm)

DTA114TM

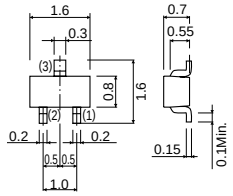


ROHM : VMT3

(1) Base
(2) Emitter
(3) Collector

Abbreviated symbol : 94

DTA114TE

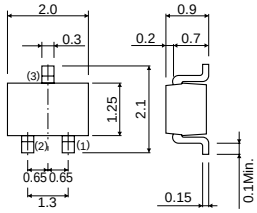


ROHM : EMT3

(1) Emitter
(2) Base
(3) Collector

Abbreviated symbol : 94

DTA114TUA



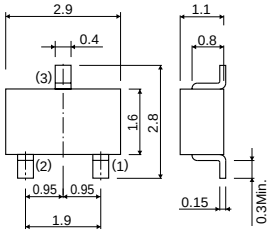
ROHM : UMT3
EIAJ : SC-70

(1) Emitter
(2) Base
(3) Collector

Each lead has same dimensions

Abbreviated symbol : 94

DTA114TKA



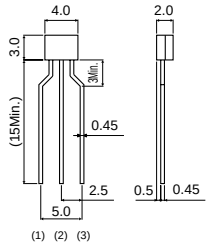
ROHM : SMT3
EIAJ : SC-59

(1) Emitter
(2) Base
(3) Collector

Each lead has same dimensions

Abbreviated symbol : 94

DTA114TSA



ROHM : SPT
EIAJ : SC-72

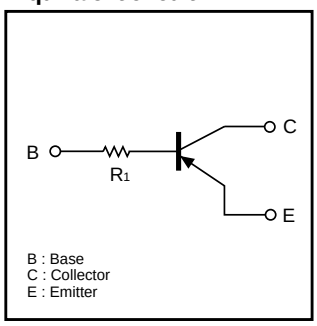
(1) Emitter
(2) Collector
(3) Base

Abbreviated symbol : A114TS

●Packaging specifications

Part No.	Package	VMT3	EMT3	UMT3	SMT3	SPT
	Package type	Taping	Taping	Taping	Taping	Taping
	Code	T2L	TL	T106	T146	TP
	Basic ordering unit (pieces)	8000	3000	3000	3000	5000
DTA114TM		○	–	–	–	–
DTA114TE		–	○	–	–	–
DTA114TUA		–	–	○	–	–
DTA114TKA		–	–	–	○	–
DTA114TSA		–	–	–	–	○

●Equivalent circuit



R_1=10kΩ

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits					Unit
		DTA114TM	DTA114TE	DTA114TUA	DTA114TKA	DTA114TSA	
Collector-base voltage	V_{CBO}	–50					V
Collector-emitter voltage	V_{CEO}	–50					V
Emitter-base voltage	V_{EBO}	–5					V
Collector current	I_C	–100					mA
Collector power dissipation	P_C	150		200		300	mW
Junction temperature	Tj	150					°C
Storage temperature	Tstg	–55 to +150					°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	–50	–	–	V	I_C=–50μA
Collector-emitter breakdown voltage	BV_{CEO}	–50	–	–	V	I_C=–1mA
Emitter-base breakdown voltage	BV_{EBO}	–5	–	–	V	I_E=–50μA
Collector cutoff current	I_{CBO}	–	–	–0.5	μA	V_{CB}=–50V
Emitter cutoff current	I_{EBO}	–	–	–0.5	μA	V_{EB}=–4V
Collector-emitter saturation voltage	$V_{CE(sat)}$	–	–	–0.3	V	I_C/I_B=–10mA/–1mA
DC current transfer ratio	h_{FE}	100	250	600	–	V_{CE}=–5V, I_C=–1mA
Input resistance	R_1	7	10	13	kΩ	–
Transition frequency	f_T *	–	250	–	MHz	V_{CE}=–10V, I_E=5mA, f=100MHz

* Characteristics of built-in transistor

●Electrical characteristic curves

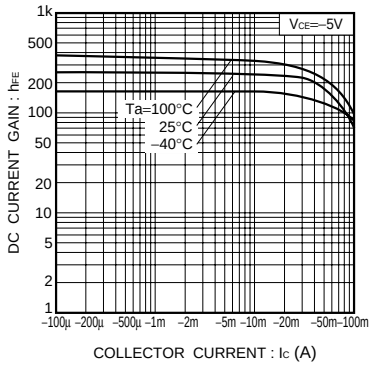


Fig.1 DC current gain vs. collector current

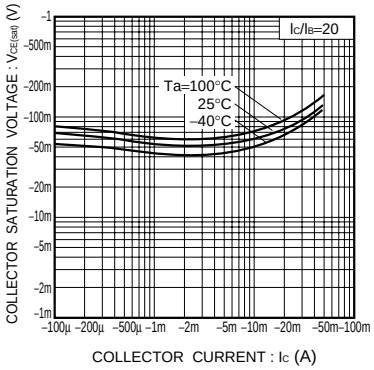


Fig.2 Collector-emitter saturation voltage vs. collector current

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